

FIG.1

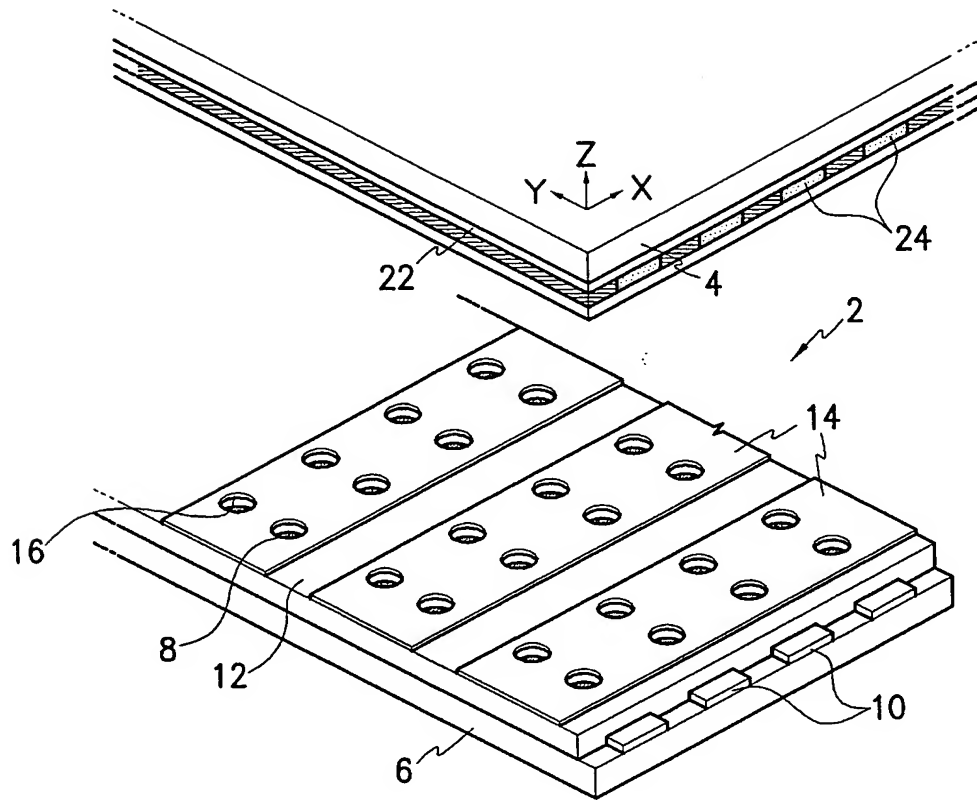


FIG.2

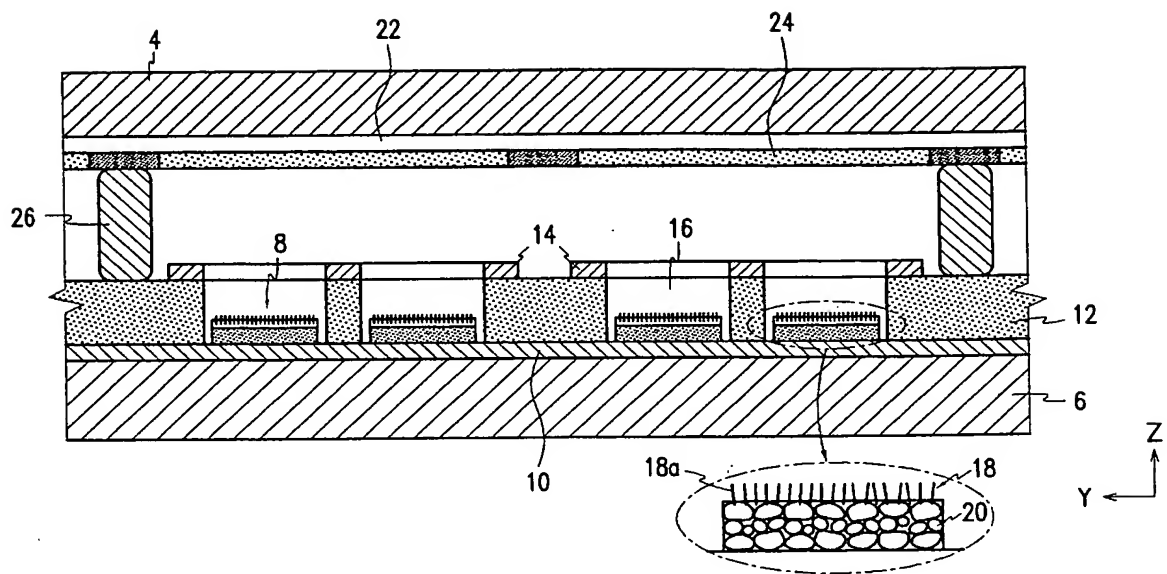


FIG.3

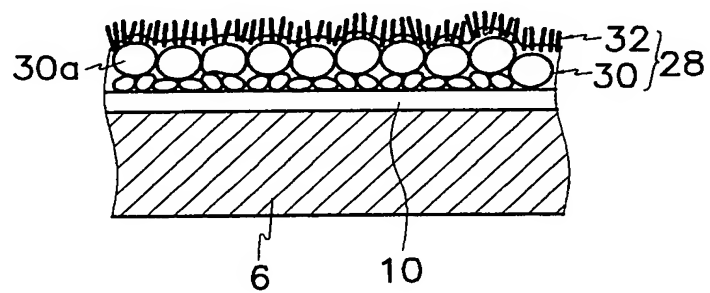


FIG.4

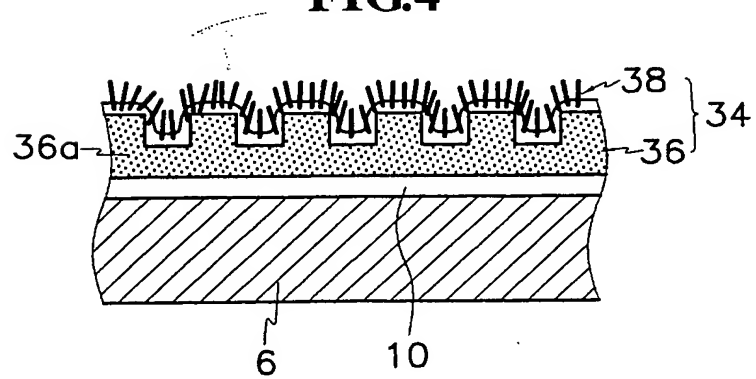
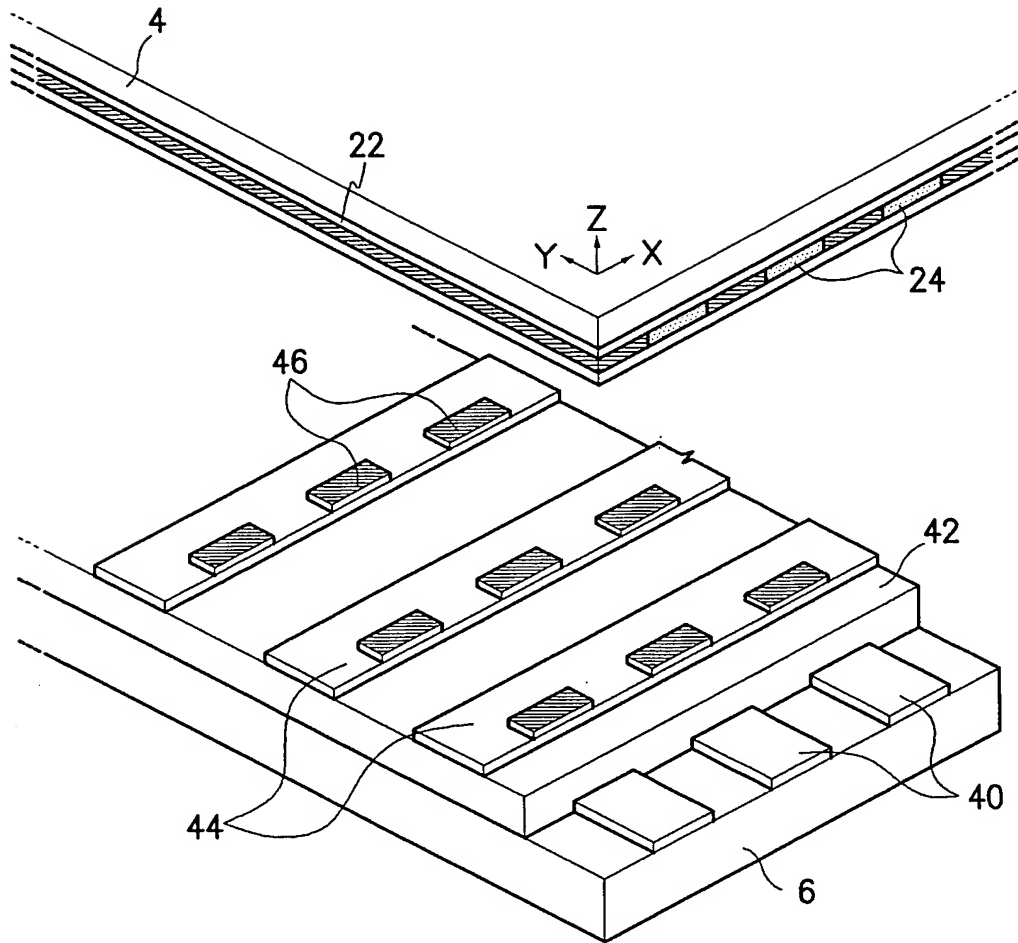


FIG.5



A cross-sectional view of a semiconductor device 100. The device features a substrate 40 with a top layer 4. A central region 22 is defined by side walls 24. Within this central region, there are several layers: a bottom layer 44, a middle layer 46, and a top layer 42. The device is shown in a cross-section along the Y-Z plane, with the Z-axis pointing upwards and the Y-axis pointing to the left.

FIG.7

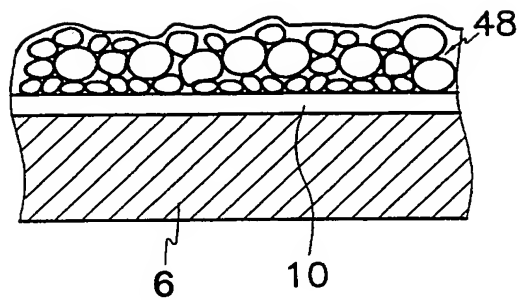


FIG.8

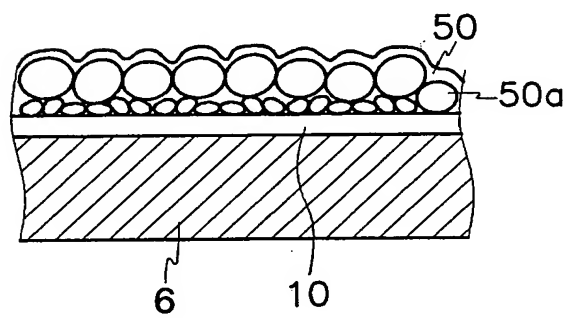


FIG.9

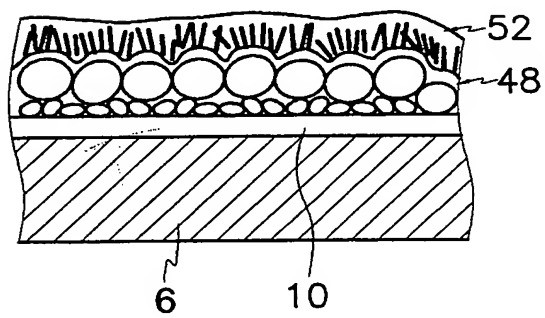


FIG.10

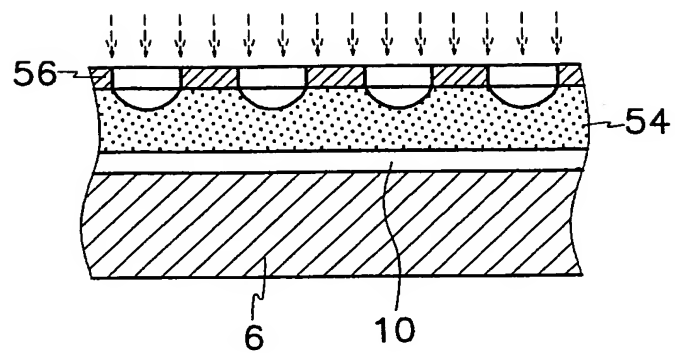


FIG.11

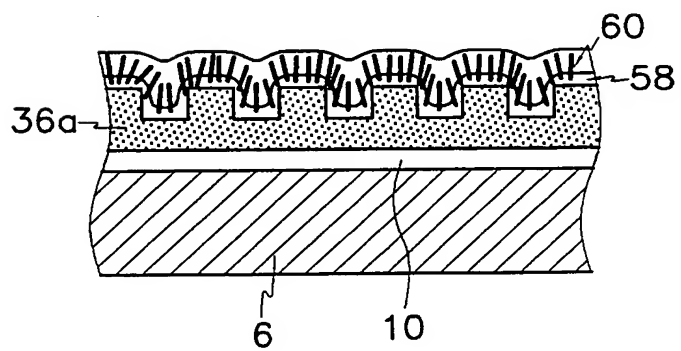


FIG.12

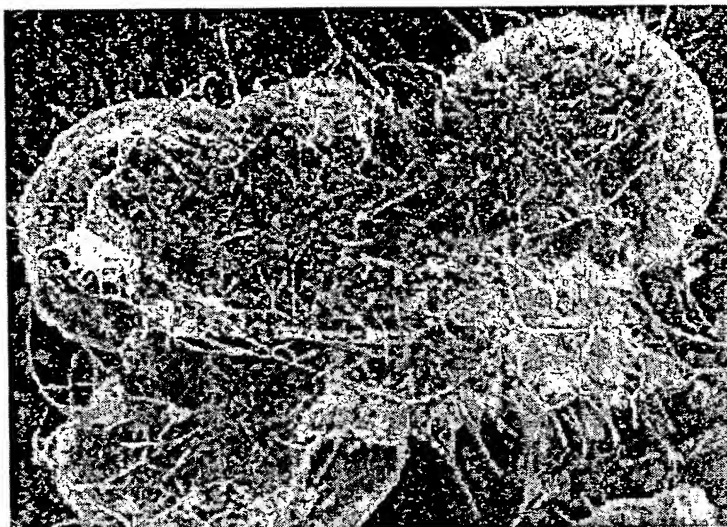


FIG.13

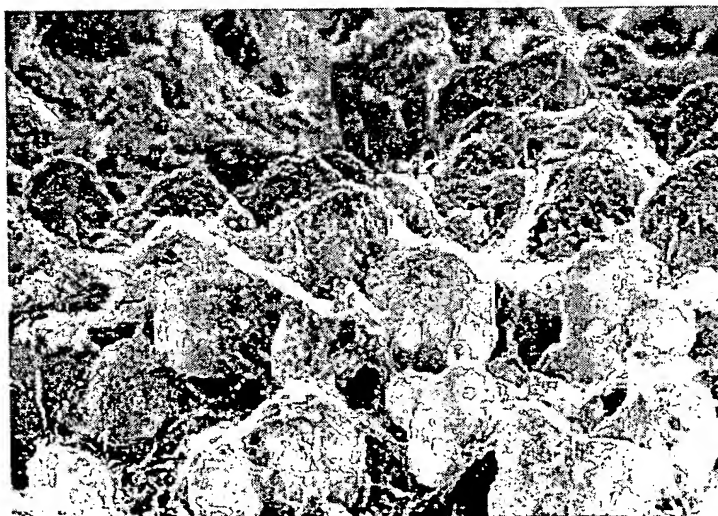


FIG.14

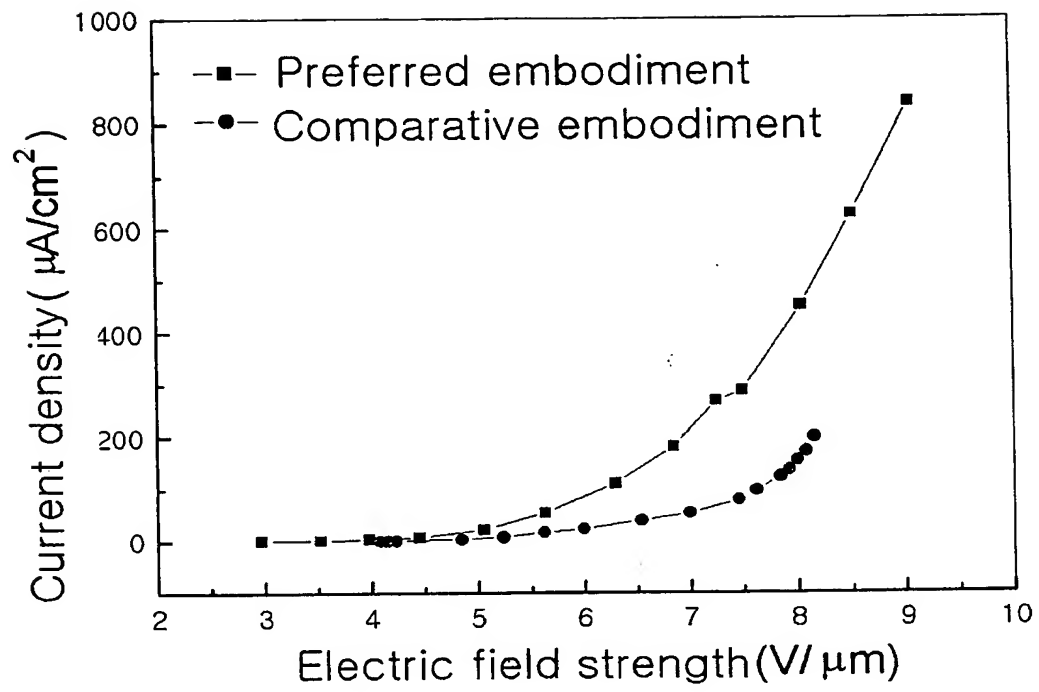


FIG.15

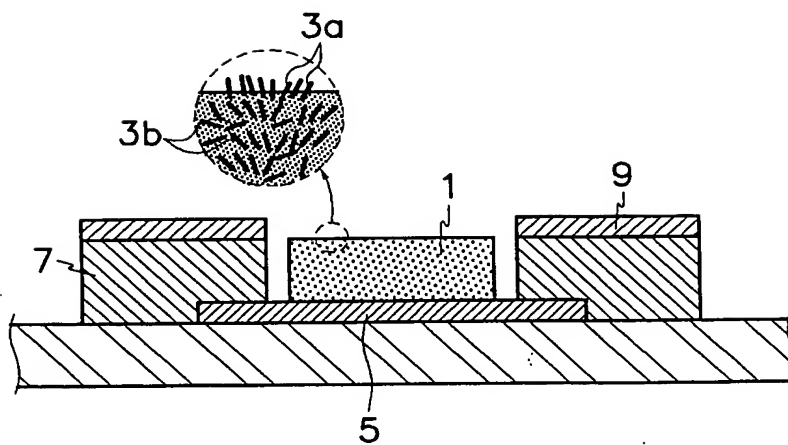


FIG.16

